

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A nonvolatile semiconductor memory storage device[[,]] ~~which is electrically writable and erasable~~, comprising:

- a semiconductor substrate;
- a plurality of element isolation portions which ~~project from the substrate and are~~ disposed at a predetermined interval on a surface portion of the semiconductor substrate;
- floating electrodes arranged on the semiconductor substrate with a first insulating film interposed in between the element isolation portions; ~~and~~
- an insulating film layer laminated formed on the element isolation portions and the floating electrodes[[,]]; ~~and~~
- a control electrode formed on the second insulating film;

wherein the adjacent floating electrodes have a plurality of step portions at opposite sides, a tapered concave portion extending from the step portions is arranged in a depth direction of the semiconductor substrate between the floating electrodes, and an interval between the adjacent floating electrodes is formed greater at the side away from the substrate than at the substrate side.

Claim 2 (Currently Amended): The nonvolatile semiconductor memory storage device according to claim 1, wherein the concave portion, into which the second insulating film is formed, extends to the element isolation portions the interval is formed from a plurality of step portions.

Claim 3 (Currently Amended): The nonvolatile semiconductor memory storage device according to claim [[2]] 1, wherein the concave portion is a V-shape sum of thickness

~~of respective step portions other than a thickness of a step portion at the most substrate side among the step portions, is 1/3 or more with respect to the sum of the thickness of all of the step portions.~~

Claim 4 (Currently Amended): The nonvolatile semiconductor memory storage device according to claim [[2]] 1, wherein the sum of thickness of respective step portions other than a thickness of a step portion at the most substrate side among the step portions of the floating electrode is 1/3 or more with respect to the sum of the thickness of all of the step portions ~~the outer circumferential length, at the insulating layer side, of the cross-section of the floating electrode is greater than or equal to 90% with respect to the sum of the cross-section, in the thickness direction and in the transverse direction, of the floating electrode.~~

Claim 5 (Currently Amended): The nonvolatile semiconductor memory storage device according to claim 1, wherein the sum of the outer circumferential length, at the second insulating layer side, of the cross-section of the floating electrode is greater than or equal to 90% with respect to the sum of the cross-section, in the thickness direction and in the transverse direction, of the floating electrode ~~a concave portion is formed on a surface, at the side away from the substrate, of the element isolation portion, and the insulating layer is formed in the concave portion.~~

Claim 6 (Currently Amended): The nonvolatile semiconductor memory storage device according to claim [[5]] 1, wherein an area of a face, which is perpendicular to the depth direction, of the concave portion is made narrower from the opening portion to the bottom portion.

Claim 7 (Canceled).

Claim 8 (New): The nonvolatile semiconductor memory device according to claim 2, wherein an area of a face, which is perpendicular to the depth direction, of the concave portion is made narrower from the opening portion to the bottom portion.

Claim 9 (New): The nonvolatile semiconductor memory device according to claim 1, wherein the element isolation portions project from the substrate.